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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



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Top View G

#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R<sub>q</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-40				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	0.0051				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.0071				
I <sub>D</sub> (A)	-100				
Configuration	Single				
Package	TO-263				

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P-Channel MOSFET	O <sub>D</sub>

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ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage	Drain-source voltage			V		
Gate-source voltage	Gate-source voltage			V		
Continuous drain current	$T_C = 25  ^{\circ}C^{a}$	I-	-100			
Continuous drain current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	-72			
Continuous source current (diode conduction) a	Is	-100	Α			
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	-300				
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-41			
Single pulse avalanche energy	L = 0.1 IIII1	E <sub>AS</sub>	84	mJ		
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	150	W		
waxiinuin powei dissipation -	T <sub>C</sub> = 125 °C		50	VV		
Operating junction and storage temperature ran	ige	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount c	$R_{thJA}$	40	°C/W		
Junction-to-case (drain)		$R_{thJC}$	1	C/VV		

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static		•			•		·
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = -250 \mu A$		-40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-250	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 \text{ V}$	-50	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A	-	0.0042	0.0051	
Drain actures on state registeres a	Б	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A, T <sub>J</sub> = 125 °C	-	-	0.0079	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A, T <sub>J</sub> = 175 °C	-	-	0.0094	Ω
	$V_{GS} = -4.5 \text{ V}$ $I_D = -25 \text{ A}$		-	0.0059	0.0071		
Forward transconductance a	9fs	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -30 A		-	103	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>				11 063	14 500	
Output capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V, f} = 1 \text{ MHz}$	-	847	1110	pF
Reverse transfer capacitance	C <sub>rss</sub>	7		-	757	1000	
Total gate charge <sup>c</sup>	$Q_g$			-	185	280	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -50 \text{ A}$	-	25	-	nC
Gate-drain charge <sup>c</sup>	$Q_{gd}$	7			30	-	1
Gate resistance	$R_g$	f = 1 MHz		1.8	3.6	5.4	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	15	25	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -20 V, $R_L$ = 0.4 $\Omega$ $I_D \cong$ -50 A, $V_{GEN}$ = -10 V, $R_g$ = 1 $\Omega$		-	180	280	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	145	220	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	160	250	
Source-Drain Diode Ratings and Char	acteristics b						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-300	А
Forward voltage	V <sub>SD</sub>	le =	-	-0.84	-1.5	V	

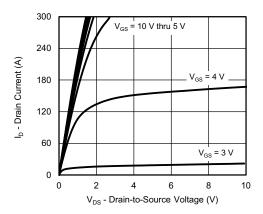
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

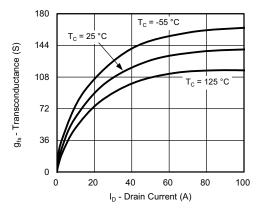
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



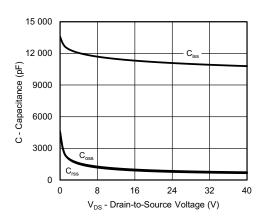
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



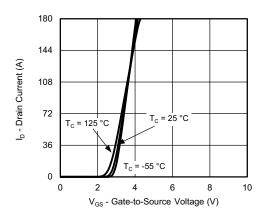
#### **Output Characteristics**



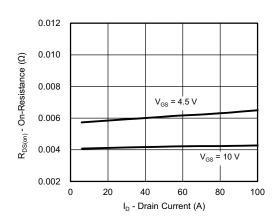
Transconductance



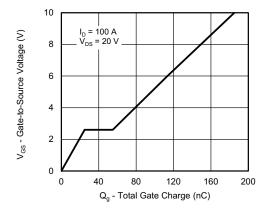
Capacitance



**Transfer Characteristics** 



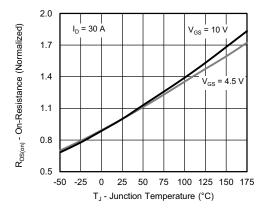
On-Resistance vs. Drain Current



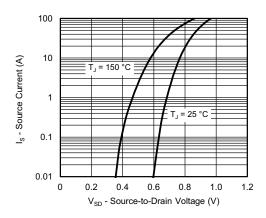
**Gate Charge** 



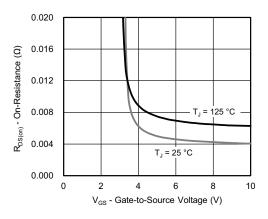
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



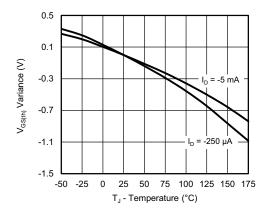
On-Resistance vs. Junction Temperature



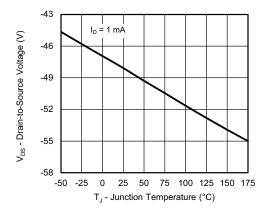
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



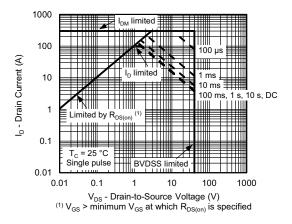
Threshold Voltage



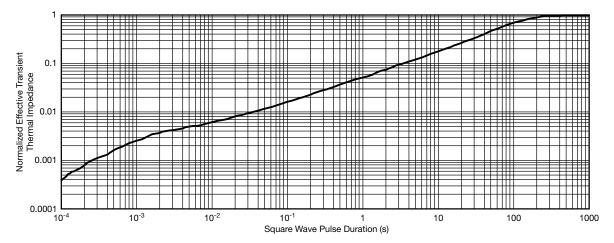
Drain Source Breakdown vs. Junction Temperature



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



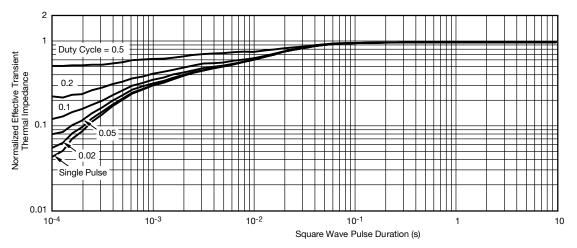
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

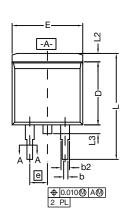
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

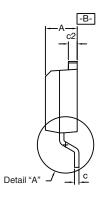
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

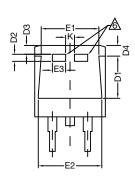
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg275728">www.vishay.com/ppg275728</a>.



# TO-263 (D<sup>2</sup>PAK): 3-LEAD

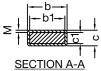








DETAIL A (ROTATED 90°)



_   <del>  -</del> b1 <del></del>    , , ,	
≥ <del>                                    </del>	- -

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

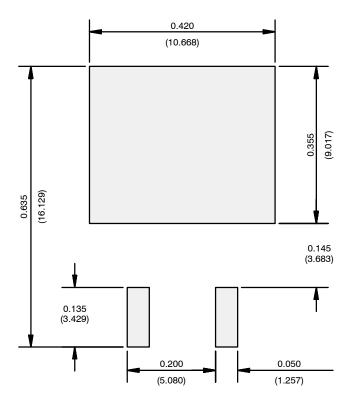
		INCHES		MILLIN	METERS
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
Е		0.380	0.410	9.652	10.414
	E1	E1 0.245 - 6.223		6.223	=
E2		0.355	0.355 0.375 9.017 9.52		9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	) BSC	2.54 BSC	
	K	0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
	L4	0.010 BSC		0.254	BSC
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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